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Long Term Operation of 4.5kV PiN and 2.5kV JBS Diodes

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#	Paper	IF	Citations
227	Luminescence from stacking faults in 4H SiC. 2001 , 79, 3944-3946		98
226	Defects in 4H silicon carbide. 2001 , 308-310, 675-679		10
225	Recombination-enhanced defect motion in forward-biased 4H-BiC p-n diodes. <i>Journal of Applied Physics</i> , 2002 , 92, 4699-4704	2.5	91
224	Recombination-enhanced extension of stacking faults in 4H-SiC p-i-n diodes under forward bias. 2002 , 81, 883-885		154
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221	Structural instability of 4H-BiC polytype induced by n-type doping. 2002 , 80, 2111-2113		116
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